INCH-POUND
MIL-M-38510/303D
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SUPERSEDING
MIL-M-38510/303C
12 November 1987

MILITARY SPECIFICATION

MICROCIRCUITS, DIGITAL, BIPOLAR LOW-POWER SCHOTTKY TTL, NOR GATES, MONOLITHIC SILICON

Inactive for new design after 18 April 1997.

This specification is approved for use by all Departments and Agencies of the Department of Defense.

1. SCOPE

- 1.1 <u>Scope.</u> This specification covers the detail requirements for monolithic silicon, low-power Schottky TTL, positive NOR logic gating microcircuits. Two product assurance classes and a choice of case outlines and lead finishes are provided for each type and are reflected in the complete part number. For this product, the requirements of MIL-M-38510 have been superseded by MIL-PRF-38535, (see 6.3).
 - 1.2 Part number. The part number shall be in accordance with MIL-PRF-38535, and as specified herein.
 - 1.2.1 <u>Device types</u>. The device types shall be as follows:

Device type	<u>Circuit</u>
01	Quadruple, 2-input positive NOR gate
02	Triple, 3-input positive NOR gate
03	Quadruple, 2-input exclusive NOR gate (open collector output)

- 1.2.2 Device class. The device class shall be the product assurance level as defined in MIL-PRF-38535.
- 1.2.3 Case outlines. The case outlines shall be as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
Α	GDFP5-F14 or CDFP6-F14	14	Flat pack
В	GDFP4-14	14	Flat pack
С	GDIP1-T14 or CDIP2-T14	14	Dual-in-line
D	GDFP1-F14 or CDFP2-F14	14	Flat pack
Χ	CQCC2-N20	20	Square leadless chip carrier
2	CQCC1-N20	20	Square leadless chip carrier

Beneficial comments (recommendations, additions, deletions) and any pertinent data which may be of use in improving this document should be addressed to: Commander, Defense Supply Center Columbus, ATTN: DSCC-VAS, 3990 East Broad St., Columbus, OH 43216-5000, by using the self addressed Standardization Document Improvement Proposal (DD Form 1426) appearing at the end of this document or by letter.

AMSC N/A FSC 5962

1.3 Absolute maximum ratings.

Supply voltage range	-1.5 V dc at -18 mA to +5.5 V dc
Device type 01	30 mW
Device type 02	
Device type 03	72 mW
Lead temperature (soldering, 10 seconds)	
Thermal resistance, junction to case (θ_{JC}):	
Cases A, B, C, D, X, and 2	(See MIL-STD-1835)
Junction temperature (T _J) <u>2</u> /	+175°C
4 Recommended operating conditions.	
Supply voltage (V _{CC})	+4.5 V dc minimum to +5.5 V dc
	maximum
Minimum high level input voltage (V _{IH})	
Maximum low level input voltage (V _{IL})	+0.7 V

2. APPLICABLE DOCUMENTS

2.1 Government documents.

2.1.1 <u>Specifications and Standards</u>. The following specifications and standards form a part of this specification to the extent specified herein. Unless otherwise specified, the issues of these documents shall be those listed in the issue of the Departments of Defense Index of Specifications and Standards (DODISS) and supplement thereto, cited in the solicitation.

Case operating temperature range (T_C) -55° to +125°C

SPECIFICATION

1.4

DEPARTMENT OF DEFENSE

MIL-PRF-38535 - Integrated Circuits (Microcircuits) Manufacturing, General Specification for.

STANDARDS

DEPARTMENT OF DEFENSE

MIL-STD-883 - Test Method Standard for Microelectronics.

MIL-STD-1835 - Interface Standard Electronic Component Case Outlines

(Unless otherwise indicated, copies of the above specifications and standards are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence.</u> In the event of a conflict between the text of this specification and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

 $[\]underline{1}$ / Must withstand the added P_D due to short-circuit test (e.g., I_{OS}).

Maximum junction temperature shall not be exceeded except for allowable short duration burn-in screening condition per method 5004 of MIL-STD-883.

3. REQUIREMENTS

- 3.1 <u>Qualification</u>. Microcircuits furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturers list before contract award (see 4.3 and 6.4).
- 3.2 <u>Item requirements</u>. The individual item requirements shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.
- 3.3 <u>Design, construction, and physical dimensions.</u> The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein.
 - 3.3.1 Terminal connections. The terminal connections shall be as specified on figure 1.
 - 3.3.2 Truth tables and logic equations. The truth tables and logic equations shall be as specified on figure 2.
- 3.3.3 <u>Schematic circuits</u>. The schematic circuits shall be maintained by the manufacturer and made available to the qualifying activity and the preparing activity (DSCC-VAS) upon request.
 - 3.3.4 Case outlines. The case outlines shall be as specified in 1.2.3.
 - 3.4 Lead material and finish. The lead material and finish shall be in accordance with MIL-PRF-38535 (see 6.6).
- 3.5 <u>Electrical performance characteristics</u>. The electrical performance characteristics are as specified in table I, and apply over the full recommended case operating temperature range, unless otherwise specified.
- 3.6 <u>Electrical test requirements</u>. The electrical test requirements for each device class shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table III.
 - 3.7 Marking. Marking shall be in accordance with MIL-PRF-38535.
- 3.8 <u>Microcircuit group assignment.</u> The devices covered by this specification shall be in microcircuit group number 8 (see MIL-PRF-38535, appendix A).

4. VERIFICATION

- 4.1 <u>Sampling and inspection.</u> Sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not effect the form, fit, or function as described herein.
- 4.2 <u>Screening.</u> Screening shall be in accordance with, MIL-PRF-38535 and shall be conducted on all devices prior to qualification and quality conformance inspection. The following additional criteria shall apply:
 - a. The burn-in test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
 - b. Interim and final electrical test parameters shall be as specified in table II, except interim electrical parameters test prior to burn-in is optional at the discretion of the manufacturer.
 - c. Additional screening for space level product shall be as specified in MIL-PRF-38535.

TABLE I. <u>Electrical performance characteristics</u>.

Test	Symbol	Condi	tions <u>1</u> /	Device	Li	mits	Unit
		-55°C ≤ T	_C ≤ +125°C	types	Min	Max	
High level output voltage	V _{OH}	$V_{CC} = +4.5 \text{ V}, V_{IN}$ $I_{OH} = -400 \mu\text{A}$	= +0.7 V,	01, 02	+2.5		V
Low level output voltage	V _{OL}	$V_{CC} = +4.5 \text{ V}, I_{OL} = V_{IN} = +2.0 \text{ V}$	= +4 mA;	All		+0.4	V
High level input	I _{IH1}	V_{CC} = +5.5 V, V_{IN}	= +2.7 V	01, 02		+20	μΑ
current				03		+40	
	I _{IH2}	$V_{CC} = +5.5 \text{ V}, V_{IN}$	= +5.5 V	01, 02		+100	μΑ
				03		+200	
Collector cut-off current	I _{CEX}	$V_{CC} = +4.5 \text{ V}, V_{IN}$ $V_{OH} = +5.5 \text{ V}$	= +0.7 V,	03		+100	μΑ
Low level input	I _{IL}	$V_{CC} = +5.5 \text{ V}, V_{IN}$	= +0.4 V	01	0	-400	μА
current				02	-30	-400]
				03	-200	-760	
Short circuit output current	los	$V_{CC} = +5.5 \text{ V} \ \underline{2}/,$ $V_{IN} = 0 \text{ V}$		01, 02	-15	-130	mA
Input clamp voltage	V _{IC}	$V_{CC} = +4.5 \text{ V}, I_{IN} = T_{C} = +25^{\circ}\text{C}$	18 mA,	All		-1.5	V
High level supply	I _{CCH}	$V_{CC} = +5.5 \text{ V}, V_{IN}$	= 0 V	01		+3.2	mA
current				02		+4.0	
Low level supply	I _{CCL}	$V_{CC} = +5.5 \text{ V}, V_{IN}$	= +4.5 V	01		+5.4	mA
current				02		+6.8	
Supply current	I _{CC}	$V_{CC} = +5.5 \text{ V } \underline{3}/$		03		+13	mA
Propagation delay time	t _{PHL}	$C_L = 50 \text{ pF} \pm 10\%$		01	2	30	ns
high-to-low level		$R_L = 2 k\Omega \pm 5\%$, V		02	2	26	
	t _{PHL1}	From A or B Other input low	$C_L = 50 \text{ pF} \pm 10\%$ $R_L = 2 \text{ k}\Omega \pm 5\%$	03	2	45	
	t _{PHL2}	From A or B Other input high	$V_{CC} = +5.0 \text{ V}$		2	45	
Propagation delay time low-to-high level	t _{PLH}	$C_L = 50 \text{ pF} \pm 10\%$ $R_L = 2 \text{ k}\Omega \pm 5\%$, V		01, 02	2	30	ns
	t _{PLH1}	From A or B Other input low	$C_L = 50 \text{ pF} \pm 10\%$ $R_L = 2 \text{ k}\Omega \pm 5\%$	03	2	56	
	t _{PLH2}	From A or B Other input high	V _{CC} = +5.0 V		2	56	

^{1/} Complete terminal conditions shall be as specified in table III.

^{2/} Not more than one output should be shorted at a time.
3/ I_{CC} is measured with one input of each gate at +4.5 V, the other inputs grounded, and the outputs open.

TABLE II. Electrical test requirements.

	Subgroups	(see table III)
MIL-PRF-38535	Class S	Class B
test requirements	devices	devices
Interim electrical parameters	1	1
Final electrical test parameters	1*, 2, 3, 9, 10, 11	1*, 2, 3, 9
Group A test requirements	1, 2, 3, 9, 10, 11	1, 2, 3, 9, 10, 11
Group C end-point electrical parameters	1, 2, 3, 9, 10, 11	1, 2, 3
Group D end-point electrical parameters	1, 2, 3	1, 2, 3

^{*}PDA applies to subgroup 1.

- 4.3 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-38535.
- 4.4 <u>Technology Conformance inspection (TCI)</u>. Technology conformance inspection shall be in accordance with MIL-PRF-38535 and herein for groups A, B, C, and D inspections (see 4.4.1 through 4.4.4).
- 4.4.1 <u>Group A inspection.</u> Group A inspection shall be in accordance with table III of MIL-PRF-38535 and as follows:
 - a. Tests shall be as specified in table II herein.
 - b. Subgroups 4, 5, 6, 7, and 8 shall be omitted.
 - 4.4.2 Group B inspection. Group B inspection shall be in accordance with table II of MIL-PRF-38535.
- 4.4.3 <u>Group C inspection.</u> Group C inspection shall be in accordance with table IV of MIL-PRF-38535 and as follows:
 - a. End-point electrical parameters shall be as specified in table II herein.
 - b. The steady-state life test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
- 4.4.4 <u>Group D inspection.</u> Group D inspection shall be in accordance with table V of MIL-PRF-38535. End-point electrical parameters shall be as specified in table II herein.
 - 4.5 Methods of inspection. Methods of inspection shall be specified and as follows.
- 4.5.1 <u>Voltage and current.</u> All voltages given are referenced to the microcircuit ground terminal. Currents given are conventional and positive when flowing into the referenced terminal.

		al symbol		al symbol	Terminal symbol			
	device	type 01	device	type 02	device type 03			
Terminal	Cases	Cases	Cases	Cases	Cases	Cases		
number	2 and X	A, B, C, D	2 and X	A, B, C, D	2 and X	A, B, C, D		
1	NC	1Y	NC	1A	NC	1A		
2	1Y	1A	1A	1B	1A	1B		
3	1A	1B	1B	2A	1B	1Y		
4	1B	2Y	2A	2B	1Y	2Y		
5	NC	2A	NC	2C	NC	2A		
6	2Y	2B	2B	2Y	2Y	2B		
7	NC	GND	NC	GND	NC	GND		
8	2A	3A	2C	3Y	2A	3A		
9	2B	3B	2Y	3A	2B	3B		
10	GND	3Y	GND	3B	GND	3Y		
11	NC	4A	NC	3C	NC	4Y		
12	3A	4B	3Y	1Y	3A	4A		
13	3B	4Y	3A	1C	3B	4B		
14	3Y	V _{CC}	3B	V _{CC}	3Y	V_{CC}		
15	NC		NC		NC			
16	4A		3C		4Y			
17	NC		NC		NC			
18	4B		1Y		4A			
19	4Y		1C		4B			
20	V_{CC}		V_{CC}		V _{CC}			

FIGURE 1. <u>Terminal connections</u>.

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Device type 01

Truth	Truth table each gate										
In	Input										
Α	В	Υ									
Н	Χ	L									
Х	Н	L									
L	L	Н									

X = Irrelevant

Positive logic: $Y = \overline{A + B}$

Device type 02

Truth table each gate										
	Input									
Α	В	C	Υ							
Н	Χ	Χ	L							
Х	Н	Χ	L							
X	Χ	Н	L							
Ĺ	Ĺ	Ĺ	Н							

X = Irrelevant

Positive logic: $Y = \overline{A + B + C}$

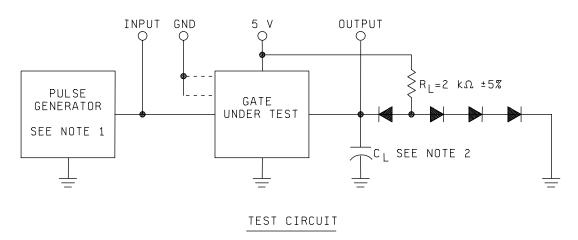
Device types 03

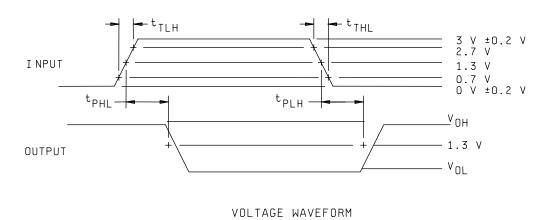
Truth table each gate										
Ir	Output									
Α	В	Υ								
L	L	Н								
L	Н	L								
Н	L	L								
Н	Н	Н								

Positive logic: $Y = \overline{A \oplus B} = AB + \overline{A} \overline{B}$

FIGURE 2. Truth tables and logic equations.

Device type 01 and 02





NOTES:

- 1. The pulse generator has the following characteristics: $t_{THL} \le 6$ ns, $t_{TLH} \le 15$ ns, PRR ≤ 1 MHz, t_P = .5 μ s, and $Z_{OUT} \cong 50 \Omega$.
- 2. $C_L = 50 \text{ pF} \pm 10\%$, including scope probe, wiring, and stray capacitance, without package in test fixture.
- 3. Voltage measurements are to be made with respect to network ground terminal.
- 4. All diodes are 1N3064 or equivalent.

FIGURE 3. Switching time test circuit and waveforms for device types 01 through 03.

DEVICE TYPE 03 $V_{CC} = 5.0 V$ $R_{L}, 2, k\Omega$ ±5% s₁0 PULSE 0 <u>-</u> **GENERATOR** SEE NOTE 1 C L / ≥50Ω ≥±5% SEE NOTE 3 TEST CIRCUIT 3 V 2.7 1.3 0.7 0 V ±0.2 V INPUT WAVEFORM ±0.2 V t_{PHL1}t_{PLH1} V_{OH} OUTPUT WAVEFORM S 1 IN POSITION B 1.3 V V_{OL} t_{PLH2}-- V_{OH} OUTPUT WAVEFORM 1.3 V S₁ IN POSITION A - V_{OL}

VOLTAGE WAVEFORM

NOTES:

- 1. The pulse generator has the following characteristics: $t_{THL} \le 6$ ns, $t_{TLH} \le 15$ ns, PRR ≤ 1 MHz, t_P = .5 μ s, and $Z_{OUT} \cong 50 \Omega$.
- 2. $C_L = 50 \text{ pF} \pm 10\%$, including scope probe, wiring, and stray capacitance, without package in test fixture.
- 3. Voltage measurements are to be made with respect to network ground terminal.
- 4. All diodes are 1N3064 or equivalent.

FIGURE 3. Switching time test circuit and waveforms for device types 01 through 03 - Continued.

TABLE III. <u>Group A inspection for device type 01</u>. Terminal conditions (pins not designated may be high \geq 2.0 V, low \leq 0.7 V, or open).

					ıer	minai co	naitions	(pins no	t designa	ited may	be nign	≥ 2.0 V,	$10W \le 0.7$	∕V, or o∣	pen).						
		MIL-STD-	Cases A,B,C,D	1	2	3	4	5	6	7	8	9	10	11	12	13	14				
Subgroup	Symbol		Cases X, 2 <u>1</u> /	2	3	4	6	8	9	10	12	13	14	16	18	19	20	Measured terminal	Lin	nits	Unit
		memod	Test no.	1Y	1A	1B	2Y	2A	2B	GND	3A	3B	3Y	4A	4B	4Y	V _{cc}	terrinia	Min	Max	
1	V _{OH}	3006	1	-400 μA	0.7 V	0.7 V		5.5 V	5.5 V	GND	5.5 V	5.5 V	- 51	5.5 V	5.5 V	71	4.5 V	1Y	2.5	IVIAA	V
	V OH	3000		-400 μΑ			400 4		0.7 V	GIND				3.5 V	J.J V		4.5 V	2Y	2.3		
$Tc = 25^{\circ}C$			2		5.5 V	5.5 V	-400 μΑ	0.7 V		"	5.5 V	5.5 V									
			3		"			5.5 V	5.5 V	"	0.7 V	0.7 V	-400 μΑ					3Y			
			4					5.5 V	5.5 V		5.5 V	5.5 V		0.7 V	0.7 V	-400 μA	"	4Y	"		
	V_{OL}	3007	5	4 mA	2.0 V	GND		GND	GND	"	GND	GND		GND	GND		"	1Y		0.4	"
		"	6	4 mA	GND	2.0 V		GND	"	tt	"	"		"	"		"	1Y		"	"
		"	7		"	GND	4 mA	2.0 V	"	"	"	"		"	"		"	2Y		"	"
		"	8			-	4 mA	GND	2.0 V	íí.		-		-	"		"	2Y		"	"
		"	9		"	"		"	GND	*	2.0 V	-	4 mA	=	-		-	3Y		"	"
		"	10			-		"		**	GND	2.0 V	4 mA		"		"	3Y			"
		"	11			-		"		"	-	GND		2.0 V	"	4 mA	"	4Y		-	"
		"	12		"			"	"	"	"	GND		GND	2.0 V	4 mA		4Y		"	"
	V _{IC}		13		- 18 mA					tt							"	1A		-1.5	"
			14			- 18 mA				"								1B		"	"
		j	15					- 18 mA		"							-	2A		"	"
			16						- 18 mA	"							"	2B		"	"
			17							"	- 18 mA						"	3A		"	"
			18							"	1011111	- 18 mA					"	3B		"	"
		i	19							"		.0		- 18 mA			"	4A		"	"
		 	20							"				1011171	- 18 mA			4B			"
	I _{IH1}	3010	21		2.7 V	GND		GND	GND	"	GND	GND		GND	GND		5.5 V	1A		20	μΑ
	'IH1	3010	22		GND	2.7 V		GND	UIVD "	"	UIVD "	UIVD "		UIVD "	UIVD		0.0 V	1B		"	μΛ
			23		GND	GND		2.7 V	"	"								2A			
			24			GND		GND	2.7 V	"								2B			
			25					GIND "	GND	"	2.7 V							3A			
			26		,,			"	UND "	"	GND	271/		-	,			3B		-	
			27		,				,	"	GIND "	2.7 V GND		2.7 V	,			4A			
					,	-				"	-	GND			0.71/					-	
			28		5.5.1					"		,		GND	2.7 V			4B		400	
	I _{IH2}		29		5.5 V			"	-	"		,			GND		- "	1A		100	
			30		GND	5.5 V				"								1B			
			31		,	GND		5.5 V				- "						2A			
			32		"			GND "	5.5 V			"			- "			2B			
			33		"	"		"	GND	"	5.5 V							3A		- "	
			34						- "	"	GND	5.5 V						3B			
		"	35		"			"			"	GND		5.5 V	= = : :		-	4A		"	
		"	36			"		"		"	"	GND		GND	5.5 V		-	4B			"
	I _{IL} <u>2</u> /	3009	37		0.4 V	5.5 V		5.5 V	5.5 V	tt.	5.5 V	5.5 V		5.5 V	"		"	1A	2/	2/	"
1		"	38		5.5 V	0.4 V		5.5 V	"	"	"	"		"	-			1B	"	"	
1		"	39		"	5.5 V		0.4 V	"	"	"	"		=	-		-	2A	-	"	"
1		"	40		=	=		5.5 V	0.4 V	"	"	-		=	"		"	2B	=	"	"
1		"	41		"	"		"	5.5 V	"	0.4 V	"		"	"		"	3A	"	"	"
1		"	42		"	-		"	"	ű	5.5 V	0.4 V		"	"		"	3B	"	"	"
1		"	43		"	"		"	"	í,	"	5.5 V		0.4 V	"		"	4A	"	"	"
		"	44		"			"	"	"	"	5.5 V		5.5 V	0.4 V		"	4B	"	"	"
	I _{OS} 3/	3011	45	GND	GND	GND				ii .							"	1Y	<u>3</u> /	<u>3</u> /	mA
		"	46				GND	GND	GND	"							"	2Y	"	"	"
1		"	47							"	GND	GND	GND				"	3Y	"	"	"
l .			48					İ		"				GND	GND	GND	"	4Y	"	"	"

See footnotes at end of device type 01

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TABLE III. <u>Group A inspection for device type 01</u> – Continued. Terminal conditions (pins not designated may be high $\geq 2.0 \text{ V}$, low $\leq 0.7 \text{ V}$, or open).

Subgroup Symbol Miles Symbol Miles Symbol Miles Cases 2 3 4 6 8 9 10 12 13 14 16 18 19 20 Measured Limits							minai cor							OW <u>></u> 0.7	v, or op							
Part			MIL-STD-		1	2	3	4	5	6	7	8	9	10	11	12	13	14				i
Test no.	Subgroup	Symbol			2	3	4	6	8	9	10	12	13	14	16	18	19	20		Lim	nits	Unit
1			motriou		1Y	1A	1B	2Y	2A	2B	GND	3A	3B	3Y	4A	4B	4Y	Vcc		Min	Max	•
Same tests, terminal conditions and limits as for subgroup 1, except T _G = +125°C and V _G tests are omitted. Same tests, terminal conditions and limits as for subgroup 1, except T _G = -55°C and V _G tests are omitted. Same tests, terminal conditions and limits as for subgroup 1, except T _G = -55°C and V _G tests are omitted. Same tests, terminal conditions and limits as for subgroup 1, except T _G = -55°C and V _G tests are omitted. Same tests, terminal conditions and limits as for subgroup 1, except T _G = -55°C and V _G tests are omitted. Same tests, terminal conditions and limits as for subgroup 1, except T _G = -55°C and V _G tests are omitted. Same tests, terminal conditions and limits as for subgroup 1, except T _G = -55°C and V _G tests are omitted. Same tests, terminal conditions and limits as for subgroup 1, except T _G = -55°C and V _G tests are omitted. Same tests, terminal conditions and limits as for subgroup 1, except T _G = -55°C and V _G tests are omitted. Same tests, terminal conditions and limits as for subgroup 1, except T _G = -55°C and V _G tests are omitted. Same tests, terminal conditions and limits as for subgroup 1, except T _G = -55°C and V _G tests are omitted. Same tests, terminal conditions and limits as for subgroup 1, except T _G = -55°C and V _G tests are omitted. Same tests, terminal conditions and limits as for subgroup 1, except T _G = -55°C and V _G tests are omitted. Same tests, terminal conditions and limits as for subgroup 1, except T _G = -55°C and V _G tests are omitted. Same tests, terminal conditions and limits as for subgroup 1, except T _G = -55°C and V _G tests are omitted. Same tests, terminal conditions and limits as for subgroup 1, except T _G = -55°C and V _G tests are omitted. Same tests, terminal conditions and limits as for subgroup 1, except T _G = -55°C and V _G tests are omitted. Same tests, terminal conditions and limits as for subgroup 1, except T _G = -55°C and V _G tests are omitted. Same tests, terminal condit	1	I _{CCH}	3005																V _{CC}			mA
Same Same Same Same Same	Tc = 25°C	I _{CCL}	3005	50		4.5 V	4.5 V		4.5 V	4.5 V	GND	4.5 V	4.5 V		4.5 V	4.5 V		5.5 V	V _{cc}		5.4	mA
To = 25°C Fill Fil																						
TC = 25°C Fig. 3	3	Same te	sts, terminal	conditions a	and limits a	s for subo	group 1, e	xcept T _C =	55°C aı	nd V _{IC} test	s are omi	ted.										
Total Fig. 5	9	t_{PHL}																				
10 Tr = 125°C Tr 10 Tr 1	Tc = 25°C		Fig. 3	52	OUT	GND	IN				"							•	1B to 1Y	"	"	"
10 Tc = 125°C Fig. Fig			"	53				OUT	IN	GND	"							=	2A to 2Y	=	"	"
10 10 10 10 10 10 10 10			"	54				OUT	GND	IN	"							=	2B to 2Y	=	"	"
Figh Second Sec				55							"	IN	GND	OUT				=	3A to 3Y	=	"	"
Fight Section Sectio			"	56							"	GND	IN	OUT					3B to 3Y	=	"	"
The control of the			"	57							"				IN	GND	OUT	"	4A to 4Y		"	"
Color Colo				58							"				GND	IN	OUT	"	4B to 4Y	=	"	"
Fig.		t _{PLH}		59	OUT	IN	GND				"							"	1A to 1Y	"	22	"
10			"	60	OUT	GND	IN				"							"	1B to 1Y	"	"	"
10 10 10 10 10 10 10 10			"	61				OUT	IN	GND	"							"	2A to 2Y		"	"
10			"	62				OUT	GND	IN	"							"	2B to 2Y	"	"	"
10			"	63							"	IN	GND	OUT				"	3A to 3Y		"	"
10 TC = 125°C TC = 125			"	64							"	GND	IN	OUT				"	3B to 3Y	"	"	"
10 Tc = 125°C 10			"	65							"				IN	GND	OUT		4A to 4Y	=	"	"
TC = 125°C 1			"	66							"				GND	IN	OUT	"	4B to 4Y	"	"	"
10 10 10 10 10 10 10 10	10	t _{PHL}		67	OUT	IN	GND				"							"	1A to 1Y		26	"
1	Tc = 125°C		"	68	OUT	GND	IN				"							"	1B to 1Y	"	"	"
To Cot GND IN			"	69				OUT	IN	GND	"							"	2A to 2Y	"	"	"
1			"	70				OUT	GND	IN	"								2B to 2Y	=	"	"
T2			"	71							"	IN	GND	OUT				"	3A to 3Y	"	"	"
Total Tota			"	72							"	GND	IN	OUT				"	3B to 3Y	"	"	"
t _{PLH}			"	73							"				IN	GND	OUT	"	4A to 4Y	"	"	"
TO TO TO TO TO TO TO TO			"	74							"				GND	IN	OUT	"	4B to 4Y	"	"	"
To To To To To To To To		t _{PLH}	"	75	OUT	IN	GND				"							"	1A to 1Y	"	30	"
78 OUT GND IN " IN GND OUT " 28 to 2Y " " " " " " " " " " " " " " " " " "			"	76	OUT	GND	IN				"							"	1B to 1Y	"	"	"
1			"	77				OUT	IN	GND	"							"	2A to 2Y	"	"	"
1			"	78				OUT	GND	IN	"							"	2B to 2Y	"	"	"
81			"								"	IN	GND	OUT				"	3A to 3Y	"	"	"
" 81 " IN GND OUT " 4A to 4Y " " " 82 " GND IN OUT " 4B to 4Y " " "			"	80							"	GND	IN	OUT				"	3B to 3Y	"	"	"
			"								"				IN	GND	OUT	"		"	"	"
			"	82							"				GND	IN	OUT	"	4B to 4Y	"	"	"
	11	Same tes	sts, terminal o	conditions a	nd limits as	s for suba	roup 10. e	except To	= -55° C.			•			•		•					

 $[\]underline{1/}$ For cases X and 2, pins not referenced are NC. $\underline{2/}$ I_{IL} limits in μA shall be as follows:

				Circuits			
Parameters	Α	В	С	D	E	F	G
I _{IL}	-0/-360	-30/-300	-160/-400	-120/-360	-150/-380	-100/-340	-160/-400

 $^{3/}I_{OS}$ limits for circuits A, B, C, D, E, and F are -15/-100 mA; for circuit G, -30/-130 mA.

TABLE III. Group A inspection for device type 02. Terminal conditions (pins not designated may be high \geq 2.0 V, low \leq 0.7 V, or open).

					I ei	rminal co	nditions	(pins no	t designa	ited may	be high	\geq 2.0 V,	$10W \le 0$.	7 V, or o	pen).						
		MIL-STD-	Cases A,B,C,D	1	2	3	4	5	6	7	8	9	10	11	12	13	14				
Subgroup	Symbol	883 method	Cases X, 2 1/	2	3	4	6	8	9	10	12	13	14	16	18	19	20	Measured terminal	Lin	nits	Unit
			Test no.	1A	1B	2A	2B	2C	2Y	GND	3Y	3A	3B	3C	1Y	1C	V _{cc}		Min	Max	
1	V _{OH}	3007	1	0.7 V	0.7 V	5.5 V	5.5 V	5.5 V		GND		5.5 V	5.5 V	5.5 V	-400 μA	0.7 V	4.5 V	1Y	2.5	max	V
Tc = 25°C	V OH	"	2	5.5 V	5.5 V	0.7 V	0.7 V	0.7 V	-400 μΑ	"		5.5 V	5.5 V	5.5 V	400 μ/ι	5.5 V	"	2Y	"		"
10 = 23 0			3	5.5 V	5.5 V	5.5 V	5.5 V	5.5 V	-400 μΑ	"	400 4	0.7 V	0.7 V	0.7 V		5.5 V	"	3Y	-		"
										"	-400 μΑ										"
	Vol	3007	4	2.0 V	GND	GND	GND	GND				GND	GND	GND	4 mA	GND		1Y	——	0.4	
			5	GND	2.0 V	"	"	"		"		"		"	"	GND	"	1Y	L		"
		"	6	"	GND	"	"	"		"		"	"	"	"	2.0 V	"	1Y			"
		"	7	"	"	2.0 V	"	"	4 mA	"		"	"	"		GND	"	2Y		"	"
		"	8	"	"	GND	2.0 V	"	"	ű		-	"	-		-	"	2Y	<u> </u>	"	"
		"	9	"	"	"	GND	2.0 V	"	"		-	"	=		-	"	2Y	<u> </u>	"	"
		"	10	"	"	-	-	GND		"	4 mA	2.0 V	"	-		-	"	3Y			"
		"	11	"		-	"	"		"	-	GND	2.0 V	"		"	"	3Y		-	"
1		"	12	"	"	"	"	"		"	"	GND	GND	2.0 V			"	3Y		"	"
1	V _{IC}		13	-18mA						"			1				"	1A		-1.5	"
1		j	14		-18mA					"							"	1B	f	"	"
			15			-18mA				**							"	2A		"	"
		i	16			1011111	-18mA			"							"	2B		"	"
			17				1011171	-18mA		"							"	2C		ű	"
		+	18					- TOTTIA		"		-18mA					"	3A	—	"	"
			19							"		- TOTTIA	-18mA				"	3B	\vdash		
		-	20							"			- TOTTIA	-18mA			"	3C		"	"
										"				-10IIIA		4 O A					
		0040	21	0.71/	ONE	ONE	ONID	OND		"		OND	OND	ONE		-18mA	· · ·	1C		00	
	I _{IH1}	3010	22	2.7 V	GND	GND	GND	GND				GND	GND	GND		GND	5.5 V	1A	——	20	μA
		"	23	GND	2.7 V	GND	"	"		"		"	"	"			"	1B	L	"	"
		"	24	"	GND	2.7 V	-	"		"			"				"	2A	L	"	"
		"	25	"	"	GND	2.7 V	"		"			"	-		-	"	2B	L	"	"
		"	26	"	"	"	GND	2.7 V		"			"	-			"	2C		"	"
		"	27	"	"	"	=	GND		*		2.7 V	-	=		=	"	3A		"	"
		"	28	"	"	-	-	"		**		GND	2.7 V	-		-	"	3B		"	"
		"	29	"		-	"	"		"		"	GND	2.7 V		"	"	3C		-	"
		"	30	"	"		"	"		"		"	"	GND		2.7 V	"	1C		"	"
	I _{IH2}	"	31	5.5 V	"	"		"		"		"	"			GND	"	1A		100	"
		"	32	GND	5.5 V	"		"		"		"	"			"	"	1B		"	"
1		"	33	"	GND	5.5 V	"	"		"		"	"	"		"	"	2A		"	"
1		"	34	"	"	GND	5.5 V	"		"		"	"	"		"	"	2B		"	"
1		"	35	"	"	"	GND	5.5 V		"		"		-			"	2C		"	"
1		"	36	"	"	"	"	GND		íí		5.5 V	"	"		"	"	3A		"	u
1		"	37	"	"	"	"	"		"		GND	5.5 V	"		"	"	3B		"	"
1		"	38	"	"	"		"		"		"	GND	5.5 V			"	3C		"	"
1			39	"	"		"	"		"		"	"	GND		5.5 V	"	1C	—	"	u
1	I _{I L} <u>2</u> /	3009	40	0.4 V	5.5 V	5.5 V	5.5 V	5.5 V		"		5.5 V	5.5 V	5.5 V		J.J V	"	1A	2/	2/	"
1	11 L <u>4</u> /	3009	41	5.5 V	0.4 V	5.5 V	3.5 V	J.J V		"		3.5 V	J.J V	3.5 V			"	1B	<u> </u>	<u>~</u> /	"
1		"	42	3.5 V	5.5 V	0.4 V	"	"		"							"	2A	"	"	"
1				-	0.0 V			-		"			-				"		"	"	"
1		p.	43	,	"	5.5 V	0.4 V	0.417		"			- "				и	2B		"	"
1			44		"		5.5 V	0.4 V		"			- "					2C	-		- "
1			45			"	- "	5.5 V		"		0.4 V		- "		E E \ ("	3A	-	"	"
1			46		"		- "					5.5 V	0.4 V			5.5 V		3B	- "		
1		"	47	"		"	"	"		"		"	5.5 V	0.4 V		5.5 V	"	3C		"	"
			48							44		"		5.5 V		0.4 V		1C		"	

See footnotes at end of device type 02

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TABLE III. Group A inspection for device type 02 – Continued. Terminal conditions (pins not designated may be high $\geq 2.0 \text{ V}$, low $\leq 0.7 \text{ V}$, or open).

					Tei	rminal co	nditions	(pins no	t designa	ated may	be high	≥ 2.0 V,	$low \leq 0$.	7 V, or o	pen).						
		MIL-STD-	Cases A,B,C,D	1	2	3	4	5	6	7	8	9	10	11	12	13	14				
Subgroup	Symbol	883 method	Cases X, 2 1/	2	3	4	6	8	9	10	12	13	14	16	18	19	20	Measured terminal	Lim	nits	Unit
			Test no.	1A	1B	2A	2B	2C	2Y	GND	3Y	3A	3B	3C	1Y	1C	V _{CC}	1 [Min	Max	ĺ
1	Ios <u>3</u> /	3011	49	GND	GND					"					GND	GND	5.5 V	1Y	<u>3</u> /	<u>3</u> /	mA
Tc = 25°C		"	50			GND	GND	GND	GND	"							"	2Y	"	"	"
		"	51							"	GND	GND	GND	GND			"	3Y	"	"	"
	I _{C C H}	3005	52	GND	GND	GND	GND	GND		GND		GND	GND	GND		GND	"	Vcc		4.0	mA
	I _{C C L}	3005	53	4.5 V	4.5 V	4.5 V	4.5 V	4.5 V		GND		4.5 V	4.5 V	4.5 V		4.5 V	. "	V _{CC}		6.8	mA
2			conditions :																		
3	Same te		conditions a			group 1, e	except T _C	= -55° C,	and V _{IC}		omitted.	•	•				•				
9	t _{PHL}	3003	54	IN	GND					GND					OUT	GND	5.0 V	1A to 1Y	2	16	ns
Tc = 25°C		(Fig. 3)	55	GND	IN					"					"	GND	"	1B to 1Y	"	"	"
		"	56	GND	GND					"					"	IN	"	1C to 1Y	**	"	"
		"	57			IN	GND	GND	OUT	"							"	2A to 2Y	"	"	"
		"	58			GND	IN	GND	"	"							"	2B to 2Y	"	"	"
		"	59			GND	GND	IN	"	"							"	2C to 2Y	"	"	"
		"	60							"	OUT	IN	GND	GND			"	3A to 3Y	"	"	"
		"	61							"	"	GND	IN	GND			"	3B to 3Y	"	"	"
		"	62							í,	"	GND	GND	IN			"	3C to 3Y	**	"	"
	t _{PLH}	"	63	IN	GND					"					OUT	GND	"	1A to 1Y	"	22	ns
		"	64	GND	IN					"					"	GND	"	1B to 1Y	"	"	"
		"	65	GND	GND					"					"	IN	"	1C to 1Y	"	"	"
		"	66			IN	GND	GND	OUT	"							"	2A to 2Y	"	"	"
		"	67			GND	IN	GND	"	"							"	2B to 2Y	"	"	"
		"	68			GND	GND	IN	"	"							"	2C to 2Y	"	"	"
		"	69							ű.	OUT	IN	GND	GND			"	3A to 3Y	"	"	"
		"	70							"	"	GND	IN	GND			"	3B to 3Y	"	"	"
		"	71							"	"	GND	GND	IN			"	3C to 3Y	"	"	"
10	t _{PHL}	"	72	IN	GND					"		0.12	0.12		OUT	GND	"	1A to 1Y	"	26	ns
Tc = 125°C	*PFIL	"	73	GND	IN					"					"	GND	"	1B to 1Y	"	"	"
10 - 120 0		"	74	GND	GND					"					"	IN	"	1C to 1Y	"	"	"
		"	75	OND	OND	IN	GND	GND	OUT	"							"	2A to 2Y	"	"	"
		"	76			GND	IN	GND	"	"							"	2B to 2Y	"	"	"
			77			GND	GND	IN	"	"							"	2C to 2Y	"	"	"
		"	78			OND	OND			"	OUT	IN	GND	GND			"	3A to 3Y	"	"	"
			79							"	"	GND	IN	GND			"	3B to 3Y	"	"	"
		"	80							"	"	GND	GND	IN			"	3C to 3Y	"	"	"
	t	"	81	IN	GND					"		GIVD	GIVD	IIN	OUT	GND	"	1A to 1Y	"	30	ns
	t _{PLH}		82	GND	IN					"					001	GND	"	1B to 1Y	"	30 "	"
			83	GND	GND					"				1		IN	"	1C to 1Y		"	"
		"	84	GIND	GIND	IN	GND	GND	OUT	"				1	-	IIN	"	2A to 2Y	"	"	"
		"	85			GND	IN	GND	"	"				1	-	1	"	2A to 2Y 2B to 2Y	"	"	"
									-	"				-	<u> </u>	-	"		"	"	"
			86			GND	GND	IN		"	OUT	INI	CND	CND	<u> </u>	-	"	2C to 2Y	"	"	"
		,	87							- "	OUT	IN	GND	GND	 	1		3A to 3Y	-		"
			88							"	- "	GND	IN	GND	-	-	"	3B to 3Y	"	"	"
			89	L	<u> </u>	l	<u> </u>		<u> </u>	l	l	GND	GND	IN	I	<u> </u>		3C to 3Y	•		
11	Same te	sts, termina	l conditions a	and limits a	as tor sub	group 10,	except T ₀	_c = -55° C	<i>;</i> .												

TABLE III. Group A inspection for device type 02 – Continued. Terminal conditions (pins not designated may be high ≥ 2.0 V, low ≤ 0.7 V, or open).

- $\underline{1}/$ For cases X and 2, pins not referenced are NC. $\underline{2}/$ I_{IL} limits in μA shall be as follows:

				Circuits			
Parameters	Α	В	С	D	E	F	G
I _{IL}	-120/-360	-30/-300	-160/-400	-120/-360	-100/-340	-160/-400	-150/-380

3/ Ios limits for circuits A, B, C, D, E, and F are -15/-100 mA; for circuit G, -30/-130 mA.

TABLE III. <u>Group A inspection for device type 03</u>. Terminal conditions (pins not designated may be high \geq 2.0 V, low \leq 0.7 V, or open).

						rminal co	naitions	(pins no	t designa	ated may	be nign	≥ 2.0 V,	10W ≤ 0.	7 V, OI O	pen).						
		MIL-STD-	Cases A,B,C,D	1	2	3	4	5	6	7	8	9	10	11	12	13	14				
Subgroup	Symbol		Cases X, 2 <u>1</u> /	2	3	4	6	8	9	10	12	13	14	16	18	19	20	Measured terminal	Lir	nits	Unit
		momod	Test no.	1A	1B	1Y	2Y	2A	2B	GND	3A	3B	3Y	4Y	4A	4B	V _{cc}	tomma	Min	Max	1
1	Vol	3007	1	0.7 V	2.0 V	4 mA		5.5 V	5.5 V	GND	5.5 V	5.5 V	- 01		5.5 V	5.5 V	4.5 V	1Y	IVIIII	0.4	V
Tc = 25°C	VOL	3007	2	2.0 V	0.7 V	4 mA		5.5 V	5.5 V	"	3.3 V	U.U V			J.J V	3.5 V	4.5 V	1Y		"	"
10 = 25 C			3	5.5 V	5.5 V	7111/	4 mA	0.7 V	2.0 V	"					"		"	2Y		"	"
			4	3.3 V	5.5 V		4 mA	2.0 V	0.7 V	"	"	"			,	"	"	2Y			"
			5	,			4 IIIA	5.5 V	5.5 V	"	0.7 V	2.0 V	4 mA				"	3Y		,	-
			6	,	-			5.5 V	5.5 V	"	2.0 V	0.7 V	4 mA		,	-	"	3Y		-	
			7	"	,			"	-	66	5.5 V	5.5 V	4 IIIA	4 mA	0.7 V	2.0 V	££	4Y		"	"
			8	,						"	3.5 V	5.5 V		4 mA	2.0 V	0.7 V	"	4 T			"
	-		9	0.7 V	0.71/	5.5 V		"	-	"	"	,		4 mA		5.5 V	"	1Y		100	
	I _{CEX}				0.7 V			"	-	"		,			5.5 V	5.5 V	"	1 Y		100	μA
			10	2.0 V	2.0 V	5.5 V	5.5.1		0.71/	"		"				"		2Y			
			11	5.5 V	5.5 V		5.5 V	0.7 V	0.7 V	"	"	"									
1			12				5.5 V	2.0 V	2.0 V	"			F F \ /				μ	2Y			-
			13					5.5 V	5.5 V	"	0.7 V	0.7 V	5.5 V			- "		3Y			- "
			14							"	2.0 V	2.0 V	5.5 V	5.5.7	0.71/			3Y			
			15						- "		5.5 V	5.5 V		5.5 V	0.7 V	0.7 V		4Y			
	.,		16	"	- "					"	5.5 V	5.5 V		5.5 V	2.0 V	2.0 V		4Y			
	V _{IC}		17	-18 mA						"								1A		-1.5	V
			18		-18 mA												- "	1B		- "	
			19					-18 mA		- "							- "	2A		- "	- "
			20						-18 mA	"								2B			
			21							"	-18 mA						- "	3A		- "	
			22									-18 mA					"	3B			
			23							"					-18 mA			4A			- "
	.	2212	24	0 = 17	0115			0110	0110	"	0115	0110			01/15	-18 mA		4B		"	
	I_{IH1}	3010	25	2.7 V	GND			GND	GND		GND	GND			GND	GND	5.5 V	1A		40	μΑ
			26	GND	2.7 V			GND	"	ű		"			"	"	"	1B		"	
			27	"	GND			2.7 V				"				"		2A			
		"	28	"	"			GND	2.7 V	íí	"	"			"	"	"	2B		"	"
		"	29	"	"			"	GND	"	2.7 V	"			"	"	"	3A		"	"
		"	30	"	"			"	"	íí	GND	2.7 V			"	"	"	3B		"	"
		"	31	"	"			"	"	ű	"	GND			2.7 V	"	"	4A		"	"
			32	"	"			"	"	"	"	"			GND	2.7 V	"	4B		"	"
	I_{1H2}		33	5.5 V	"			"		"	"				"	GND	"	1A		200	- "
			34	GND	5.5 V			"		"	"	"					- "	1B		- "	
			35		GND			5.5 V		"							"	2A			└ "
			36					GND	5.5 V	- "		"					"	2B			
1			37		"			"	GND	"	5.5 V	"				"	"	3A		- "	- "
1			38	"	"			"		"	GND	5.5 V					"	3B		"	- "
1			39	"	"			"		"	"	GND			5.5 V		"	4A		"	- "
1			40		"			"		"	"	GND			GND	5.5 V	"	4B		"	"
	I _{I L} <u>2</u> /	3009	41	0.4 V	5.5 V			5.5 V	5.5 V	"	5.5 V	5.5 V			5.5 V		"	1A	2/	<u>2</u> /	- "
			42	5.5 V	0.4 V			5.5 V		"	"	"					"	1B	"	"	
			43	"	5.5 V			0.4 V	"	"		"			"		"	2A	"	"	
		"	44	"	"			5.5 V	0.4 V	"	"	"			"	"	"	2B	"	"	"
		"	45	"	"			"	5.5 V	"	0.4 V	"			"	"	"	3A	"	"	"
		"	46	"	"			"	"	"	5.5 V	0.4 V			"	"	"	3B	"	"	"
		"	47 48	"	"			"	"	"	"	5.5 V 5.5 V			0.4 V	"		4A 4B			↓
										66					5.5 V	0.4 V					

See footnotes at end of device type 03.

TABLE III. <u>Group A inspection for device type 03</u> – Continued.

Terminal conditions (pins not designated may be high > 2.0 V, low < 0.7 V, or open).

					ı eri	minal cor	naitions	(pins not	designa	tea may	be nign	≥ 2.0 V, I	$OW \leq U.7$	v, or op	en).						
		MIL-STD-	Cases A,B,C,D	1	2	3	4	5	6	7	8	9	10	11	12	13	14				
Subgroup	Symbol	883 method	Cases X, 2 <u>1</u> /	2	3	4	6	8	9	10	12	13	14	16	18	19	20	Measured terminal	Lim	nits	Unit
			Test no.	1A	1B	1Y	2Y	2A	2B	GND	3A	3B	3Y	4Y	4A	4B	V _{cc}	1	Min	Max	1
1 Tc = 25°C	I _{C C}	3005	49	GND	4.5 V			GND	4.5 V	GND	GND	4.5 V			GND	4.5 V	5.5 V	Vcc		13	mA
2	Same te	ests, terminal	conditions	and limits	as for sub	group 1, e	except T _C	= +125° (c, and V	tests are	omitted.		•	•	•	•			•		
3	Same te	ests, terminal	conditions	and limits	as for sub	group 1, e	except T _C	= -55° C.	and V _{1C}	tests are	omitted.										
9	t _{PHL 1}	3003	50	IN	GND	OUT				GND							5.0 V	1A to 1Y	2	40	ns
Tc = 25°C		(Fig. 3)	51	GND	IN	OUT				**							"	1B to 1Y	"	"	66
		"	52				OUT	IN	GND	"							"	2A to 2Y	"	"	66
		"	53				OUT	GND	IN	"							"	2B to 2Y	"	"	66
		"	54							"	IN	GND	OUT				"	3A to 3Y	"	"	66
		"	55							"	GND	IN	OUT				"	3B to 3Y	"	"	"
		"	56							"				OUT	IN	GND	"	4A to4Y	"	"	66
		"	57							"				OUT	GND	IN	"	4B to 4Y	"	"	"
	t _{PLH 1}	"	58	IN	GND	OUT				"							"	1A to 1Y	"	45	"
		"	59	GND	IN	OUT				"							"	1B to 1Y	"	"	"
		"	60				OUT	IN	GND	"							"	2A to 2Y	"	"	66
		"	61				OUT	GND	IN	**							"	2B to 2Y	"	"	"
		"	62							**	IN	GND	OUT				"	3A to 3Y	"	"	"
		"	63							"	GND	IN	OUT				"	3B to 3Y	"	"	"
		"	64							**				OUT	IN	GND	66	4A to4Y	"	"	66
		"	65							"				OUT	GND	IN	"	4B to 4Y	"	"	"
	t _{PHL2}	"	66	IN	2.7 V	OUT				"							"	1A to 1Y		40	"
	1112	"	67	2.7 V	IN	OUT				"							"	1B to 1Y	"	"	66
		"	68				OUT	IN	2.7 V	"							"	2A to 2Y	"	"	"
		"	69				OUT	2.7 V	IN	"							"	2B to 2Y	"	"	"
		"	70							"	IN	2.7 V	OUT				"	3A to 3Y	"	"	"
		"	71							"	2.7 V	IN	OUT				"	3B to 3Y	"	"	"
		"	72							"				OUT	IN	2.7 V	"	4A to4Y	"	"	"
		"	73							"				OUT	2.7 V	IN	"	4B to 4Y	"	"	"
	t _{PLH 2}	"	74	IN	2.7 V	OUT				"							"	1A to 1Y	"	45	"
		"	75	2.7 V	IN	OUT				66							**	1B to 1Y	66	"	**
		"	76	İ	1	1	OUT	IN	2.7 V	"		1					"	2A to 2Y	"	"	"
		"	77				OUT	2.7 V	IN	"							"	2B to 2Y	"	"	"
		"	78							"	IN	2.7 V	OUT				"	3A to 3Y	"	"	"
		"	79							66	2.7 V	IN	OUT				"	3B to 3Y	"	"	"
		"	80							"				OUT	IN	2.7 V	"	4A to4Y	"	"	"
		"	81							66				OUT	2.7 V	IN	"	4B to 4Y	"	"	"

See footnotes at end of device type 03.

TABLE III. Group A inspection for device type 03 – Continued. Terminal conditions (pins not designated may be high ≥ 2.0 V, low ≤ 0.7 V, or open).

		MIL-STD-	Cases A,B,C,D	1	2	3	4	5	6	7	8	9	10	11	12	13	14				
Subgroup	Symbol	883 method	Cases X, 2 1/	2	3	4	6	8	9	10	12	13	14	16	18	19	20	Measured terminal	Lim	iits	Unit
			Test no.	1A	1B	1Y	2Y	2A	2B	GND	3A	3B	3Y	4Y	4A	4B	V _{CC}		Min	Max	
10	t _{PHL 1}	3003	82	IN	GND	OUT				GND							5.0 V	1A to 1Y	2	45	ns
Tc = 125°C		(Fig. 3)	83	GND	IN	OUT				"							66	1B to 1Y	66	66	"
		"	84				OUT	IN	GND	"							"	2A to 2Y	"	"	"
		"	85				OUT	GND	IN	"							"	2B to 2Y	"	"	"
			86							"	IN	GND	OUT				"	3A to 3Y	"	"	"
		"	87							"	GND	IN	OUT				"	3B to 3Y	"	"	"
		"	88							"				OUT	IN	GND	"	4A to4Y	"	"	"
		"	89							"				OUT	GND	IN	"	4B to 4Y	"	"	"
	t _{PLH 1}	"	90	IN	GND	OUT				"							"	1A to 1Y		56	"
		"	91	GND	IN	OUT				"							66	1B to 1Y	**	66	££
		"	92				OUT	IN	GND	"							66	2A to 2Y	66	66	66
		"	93				OUT	GND	IN	"							66	2B to 2Y	**	66	££
		"	94							"	IN	GND	OUT				"	3A to 3Y	"	"	66
		"	95							"	GND	IN	OUT				66	3B to 3Y	**	66	££
		"	96							"				OUT	IN	GND	"	4A to4Y	"	66	66
		"	97							"				OUT	GND	IN	66	4B to 4Y	66	66	66
	t _{PHL2}	"	98	IN	2.7 V	OUT				"							"	1A to 1Y	"	45	"
		"	99	2.7 V	IN	OUT				"							66	1B to 1Y	66	66	66
		"	100				OUT	IN	2.7 V	"							"	2A to 2Y	"	66	"
		"	101				OUT	2.7 V	IN	"							"	2B to 2Y	"	"	"
		"	102							"	IN	2.7 V	OUT				"	3A to 3Y	"	"	"
		"	103							"	2.7 V	IN	OUT				"	3B to 3Y	"	"	"
		"	104							"				OUT	IN	2.7 V	66	4A to4Y	"	66	"
		"	105							"				OUT	2.7 V	IN	"	4B to 4Y	"	"	"
	t _{PLH 2}	"	106	IN	2.7 V	OUT				"							"	1A to 1Y	"	56	"
		"	107	2.7 V	N	OUT				"							"	1B to 1Y	"	"	"
		"	108				OUT	IN	2.7 V	"							66	2A to 2Y	"	66	"
		"	109				OUT	2.7 V	IN	"							66	2B to 2Y	"	66	"
		"	110							"	IN	2.7 V	OUT				"	3A to 3Y	"	"	"
		"	111							"	2.7 V	IN	OUT				66	3B to 3Y	"	"	"
		"	112							"				OUT	IN	2.7 V	66	4A to4Y	"	66	"
		"	113							"				OUT	2.7 V	IN	66	4B to 4Y	"	66	**

 $[\]underline{1}/$ For cases X and 2, pins not referenced are NC. $\underline{2}/$ I_{IL} limits in μA shall be as follows:

				Circuits			
Parameters	Α	В	С	D	Е	F	G
I _{IL}	-200/-680	-230/-600	-275/-600	-230/-600	-300/-760	-200/-720	-300/-760

5. PACKAGING

5.1 <u>Packaging requirements</u>. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of materiel is to be performed by DoD personnel, these personnel need to contact the responsible packaging activity to ascertain requisite packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activity within the Military Department of Defense Agency, or within the Military Department's System Command. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

- 6.1 <u>Intended use.</u> Microcircuits conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.
 - 6.2 Acquisition requirements. Acquisition documents should specify the following:
 - a. Title, number, and date of the specification.
 - b. Complete part number (see 1.2).
 - c. Requirements for delivery of one copy of the quality conformance inspection data pertinent to the device inspection lot to be supplied with each shipment by the device manufacturer, if applicable.
 - d. Requirements for certificate of compliance, if applicable.
 - e. Requirements for notification of change of product or process to contracting activity in addition to notification to the qualifying activity, if applicable.
 - f. Requirements for failure analysis (including required test condition of method 5003 of MIL-STD-883), corrective action, and reporting of results, if applicable.
 - g. Requirements for product assurance options.
 - h. Requirements for special carriers, lead lengths, or lead forming, if applicable. These requirements should not affect the part number. Unless otherwise specified, these requirements will not apply to direct purchase by or direct shipment to the Government.
 - j. Requirements for "JAN" marking.
- 6.3 <u>Superseding information.</u> The requirements of MIL-M-38510 have been superseded to take advantage of the available Qualified Manufacturer Listing (QML) system provided by MIL-PRF-38535. Previous references to MIL-M-38510 in this document have been replaced by appropriate references to MIL-PRF-38535. All technical requirements now consist of this specification and MIL-PRF-38535. The MIL-M-38510 specification sheet number and PIN have been retained to avoid adversely impacting existing government logistics systems and contractor's parts lists.
- 6.4 <u>Qualification</u>. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List QML-38535 whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or purchase orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DSCC-VQ, 3990 E. Broad Street, Columbus, Ohio 43123-1199.

6.5 <u>Abbreviations, symbols, and definitions.</u> The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535, MIL-HDBK-1331, and as follows:

GND	Ground zero voltage potential
I _{IN}	Current flowing into an input terminal
V _{IN}	Voltage level at an input terminal

- 6.6 <u>Logistic support.</u> Lead materials and finishes (see 3.4) are interchangeable. Unless otherwise specified, microcircuits acquired for Government logistic support will be acquired to device class B (see 1.2.2), lead material and finish A (see 3.4). Longer length leads and lead forming shall not affect the part number.
- 6.7 <u>Substitutability.</u> The cross-reference information below is presented for the convenience of users. Microcircuits covered by this specification will functionally replace the listed generic-industry type. Generic-industry microcircuit types may not have equivalent operational performance characteristics across military temperature ranges or reliability factors equivalent to MIL-M-38510 device types and may have slight physical variations in relation to case size. The presence of this information shall not be deemed as permitting substitution of generic-industry types for MIL-M-38510 types or as a waiver of any of the provisions of MIL-PRF-38535.

Military device	Generic-industry
type	type
01	54LS02
02	54LS27
03	54LS266

6.8 <u>Manufacturers' designation.</u> Manufacturers' included in this specification are designated as shown in table IV herein.

TABLE IV. Manufacturers' designation.

			Manufactur	er		
Device	Circuit A	Circuit B	Circuit C	Circuit D	Circuit E	Circuit F
type	Texas Instru-	Signetics	National	Raytheon	Motorola	Fairchild
	ments Inc.	Corporation	Semiconductor	Company	Inc	Semiconductor
			Corp			
01	Α	В	С	G	E	F
02	А	В	С	F	G	E
03	А	В	С	D	Е	F

6.9 <u>Changes from previous issue.</u> Asterisks are not used in this revision to identify changes with respect to the previous issue due to the extensiveness of the changes.

Custodians: Preparing activity: Army - CR DLA - CC

Navy - EC Air Force - 11

(Project 5962-1947)

DLA - CC

Review activities:

Army - HD, MI, SM

Navy - AS, CG, MC, SH, TD

Air Force - 03, 19, 99